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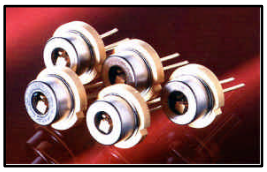
RLT8350G TECHNICAL DATA

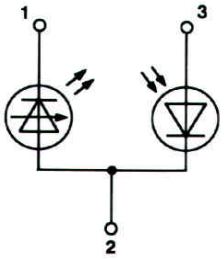


High Power Infrared Laserdiode

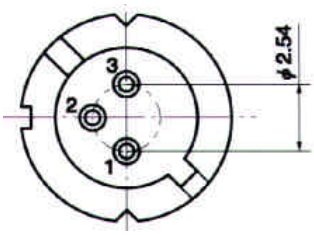
Structure: **AlGaAs/GaAs quantum well, Aperture 3 x 1.5 µm²**
Lasing wavelength: **830 nm typ.**
Max. optical power: **60 mW, single mode**
Package: **9 mm G**

NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:



1) Laser diode cathode
2) Laser diode anode and photodiode cathode
3) Photodiode anode



Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	60	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	5	V
Operating Temperature	T_C	-60 .. +60	°C
Storage Temperature	T_{STG}	-70 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o			50		mW
Threshold Current	I_{th}			20	30	mA
Operation Current	I_{op}	P_o =50mW	110	120	150	mA
Lasing Wavelength	I_p	P_o =50mW		830	840	nm
Beam Divergence	θ //	P_o =50mW		12		°
Beam Divergence	θ ⊥	P_o =50mW		25		°
Differential Efficiency	dP_o/dI_{op}	P_o =50mW		0.75		mW/mA
Monitor Current	I_m	P_o =50mW		250		µA